Erratum: Distribution of Interface States in MOS Systems Extracted by the Subthreshold Current in MOSFETs under Optical Illumination

[J. Korean Phys. Soc. **43**, 873 (2003)]
DOI: 10.3938/jkps.43.873

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DOI: 10.3938/jkps.72.326

Sentence (p. 874) in Chapter II starting with “They are ... on the device fabrication process [10-15].” should be corrected as “They are ... on the device fabrication process [10-15]. We also note that charge states in traps are gate bias-dependent [16].”.

Two paragraphs (p. 874) in Chapter II “Figure 2 shows the energy-band diagram ... the gate voltage applied across the MOS capacitor.” and “Figure 3(c) shows the condition at inversion in which there is now a net negative charge in the acceptor states [15,16].” and Figs. 2 and 3 should be removed.